

ABSTRACT OF THE DISCLOSURE

A method for fabricating a semiconductor device comprises the steps of forming a polysilicon film 32 on a silicon substrate 10, implanting a dopant into a region of the polysilicon film 32 for a resistance element to be formed in, patterning the polysilicon film 32 to form the resistance element 46 of the polysilicon film 32 with the dopant implanted in and gate electrodes 44a, 44b of the polysilicon film 32 with the dopant not implanted in. Accordingly, resistance element can be formed while suppressing influences on characteristics of the transistor formed on one and the same substrate concurrently with forming the resistance element.